MCH6342

Power MOSFET -30V, 73mΩ, -4.5A, Single P-Channel

This Power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and low on resistance. This device is suitable for applications with low gate charge driving or low on resistance requirements.

Features

- Low On-Resistance
- 1.8V drive
- High Speed Switching
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance

Typical Applications

• DC/DC Converter

SPECIFICATIONS

ABSOLUTE MAXIMUM RATING at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	-30	V
Gate to Source Voltage	VGSS	±10	V
Drain Current (DC)	۱D	-4.5	Α
Drain Current (Pulse) PW $\leq 10\mu$ s, duty cycle $\leq 1\%$	IDP	-18	А
Power Dissipation When mounted on ceramic substrate $(1500 \text{mm}^2 \times 0.8 \text{mm})$	PD	1.5	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	–55 to +150	°C

Note 1 : Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit
Junction to Ambient When mounted on ceramic substrate (1500mm ² × 0.8mm)	R _{θJA}	83.3	°C/W

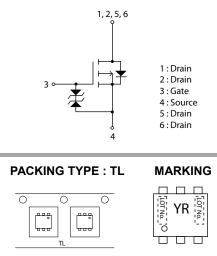


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VDSS	R _{DS} (on) Max	ID Max
	73mΩ@ –4.5V	
-30V	99mΩ@ –2.5V	-4.5A
	155mΩ@ −1.8V	

ELECTRICAL CONNECTION P-Channel



ORDERING INFORMATION

See detailed ordering and shipping information on page 5 of this data sheet.

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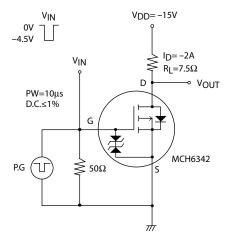
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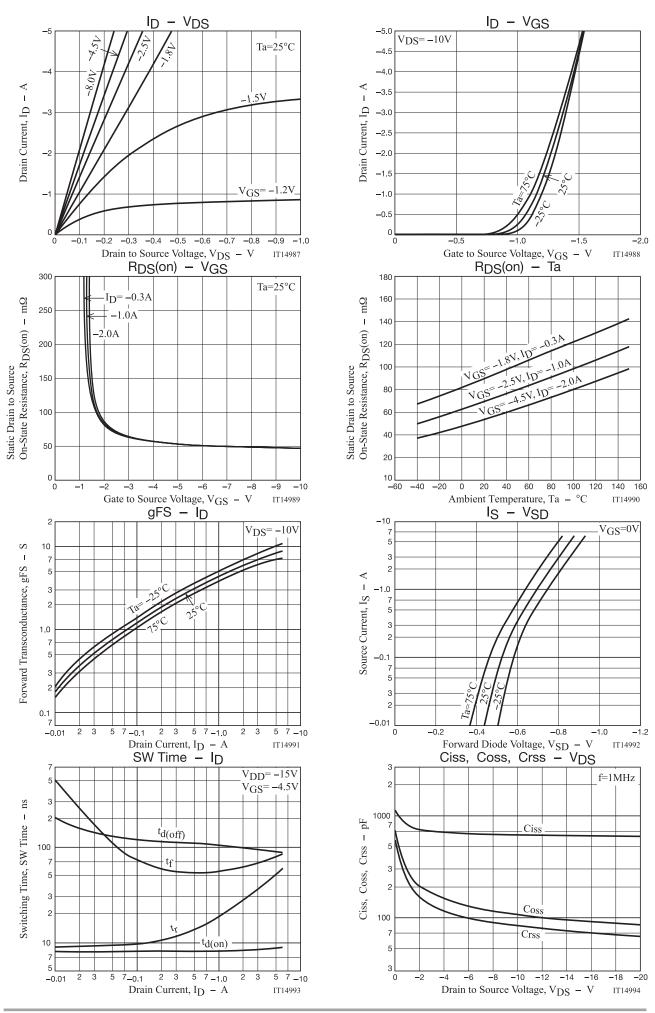
Decemeter	Cumbal	Conditions	Value			Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Drain to Source Breakdown Voltage	V(BR)DSS	ID=-1mA, VGS=0V	-30			V
Zero-Gate Voltage Drain Current	IDSS	V _{DS} =-30V, V _{GS} =0V			-1	μA
Gate to Source Leakage Current	IGSS	VGS=±8V, VDS=0V			±10	μA
Gate Threshold Voltage	VGS(th)	V _{DS} =-10V, I _D =-1mA	-0.4		-1.3	V
Forward Transconductance	9FS	V _{DS} =-10V, I _D =-2A	3.4	5.8		S
	R _{DS} (on)1	ID=-2A, VGS=-4.5V		56	73	mΩ
Static Drain to Source On-State Resistance	R _{DS} (on)2	ID=-1A, VGS=-2.5V		71	99	mΩ
Resistance	R _{DS} (on)3	ID=-0.3A, VGS=-1.8V		95	155	mΩ
Input Capacitance	Ciss	V _{DS} =–10V, f=1MHz		650		pF
Output Capacitance	Coss			105		pF
Reverse Transfer Capacitance	Crss			83		pF
Turn-ON Delay Time	t _d (on)			8.2		ns
Rise Time	tr			28		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit		100		ns
Fall Time	tf			60		ns
Total Gate Charge	Qg			8.6		nC
Gate to Source Charge	Qgs	V _{DS} =-15V, V _{GS} =-4.5V, I _D =-4.5A		1.3		nC
Gate to Drain "Miller" Charge	Qgd			2.4		nC
Forward Diode Voltage	V _{SD}	IS=-4.5A, VGS=0V		-0.83	-1.2	V

ELECTRICAL CHARACTERISTICS at Ta = $25^{\circ}C$ (Note 2)

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

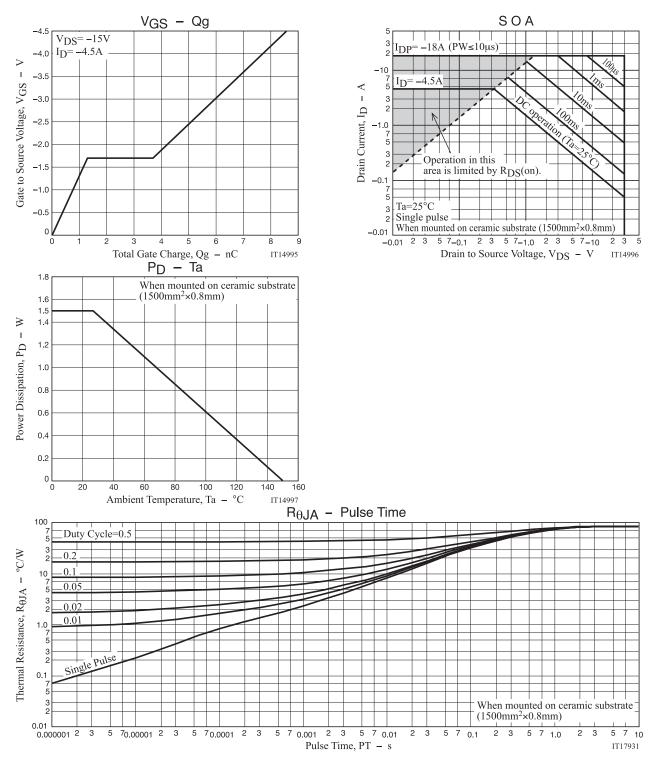
Switching Time Test Circuit





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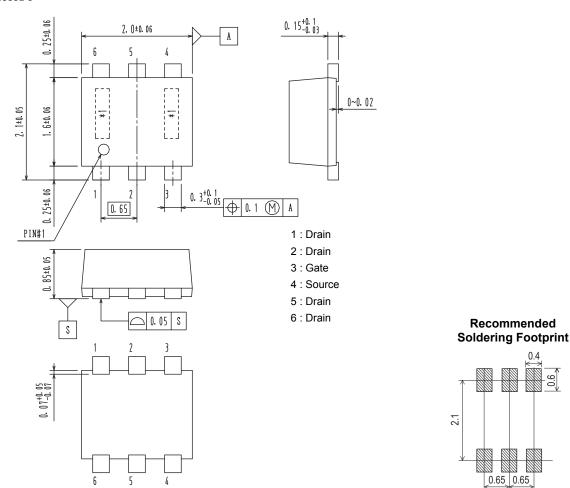
MCH6342



PACKAGE DIMENSIONS

unit : mm

SC-88FL / MCPH6 CASE 419AS ISSUE O



ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
MCH6342-TL-H	VB	SC-88FL / MCPH6	3,000 / Tape & Reel	
MCH6342-TL-W	YR	(Pb-Free / Halogen Free)		

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub_link/Collateral/BRD8011-D.PDF

Note on usage : Since the MCH6342 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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